

General Description

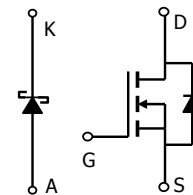
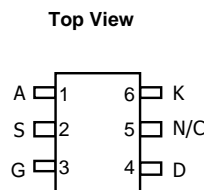
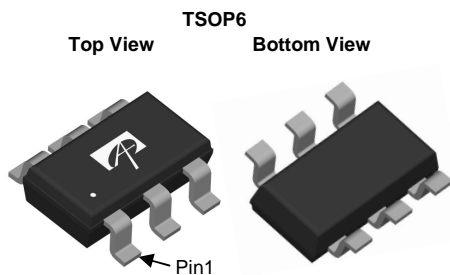
The AO6701 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. A Schottky diode is provided to facilitate the implementation of a bidirectional blocking switch, or for DC-DC conversion applications.

Product Summary

$V_{DS} (V) = -30V$
 $I_D = -2.3A (V_{GS} = -10V)$
 $R_{DS(ON)} < 135m\Omega (V_{GS} = -10V)$
 $R_{DS(ON)} < 185m\Omega (V_{GS} = -4.5V)$
 $R_{DS(ON)} < 265m\Omega (V_{GS} = -2.5V)$

SCHOTTKY

$V_{DS} (V) = 20V$
 $I_F = 1A$
 $V_F < 0.5V @ 0.5A$



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	MOSFET	Schottky	Units
Drain-Source Voltage	V_{DS}	-30		V
Gate-Source Voltage	V_{GS}	± 12		V
Continuous Drain Current ^A	$T_A=25^\circ C$	-2.3		A
	$T_A=70^\circ C$	-1.8		
Pulsed Drain Current ^B	I_{DM}	-15		
Schottky reverse voltage	V_{KA}		20	V
Continuous Forward Current ^A	$T_A=25^\circ C$		2	A
	$T_A=70^\circ C$		1	
Pulsed Forward Current ^B	I_{FM}		10	
Power Dissipation	$T_A=25^\circ C$	1.15	0.92	W
	$T_A=70^\circ C$	0.7	0.59	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ C$

Parameter: Thermal Characteristics MOSFET		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$t \leq 10s$	$R_{\theta JA}$	78	110	$^\circ C/W$
Maximum Junction-to-Ambient ^A	Steady-State		106	150	
Maximum Junction-to-Lead ^C	Steady-State	$R_{\theta JL}$	64	80	
Thermal Characteristics Schottky					
Maximum Junction-to-Ambient ^A	$t \leq 10s$	$R_{\theta JA}$	109.4	135	$^\circ C/W$
Maximum Junction-to-Ambient ^A	Steady-State		136.5	175	
Maximum Junction-to-Lead ^C	Steady-State	$R_{\theta JL}$	58.5	80	

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-24V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±12V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =-250μA	-0.6	-1	-1.4	V
I _{D(ON)}	On state drain current	V _{GS} =-4.5V, V _{DS} =-5V	-15			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-2.3A T _J =125°C		107 154	135 190	mΩ
		V _{GS} =-4.5V, I _D =-2A		135	185	mΩ
		V _{GS} =-2.5V, I _D =-1A		195	265	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-2.3A		8		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.85	-1	V
I _S	Maximum Body-Diode Continuous Current				-1.35	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, f=1MHz		409		pF
C _{oss}	Output Capacitance			55		pF
C _{rss}	Reverse Transfer Capacitance			42		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		12		Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =-4.5V, V _{DS} =-15V, I _D =-2.0A		4.9		nC
Q _{gs}	Gate Source Charge			0.6		nC
Q _{gd}	Gate Drain Charge			1.6		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-10V, V _{DS} =-15V, R _L =7.5Ω, R _{GEN} =3Ω		6.9		ns
t _r	Turn-On Rise Time			3.3		ns
t _{D(off)}	Turn-Off DelayTime			38.5		ns
t _f	Turn-Off Fall Time			13.2		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-2.0A, di/dt=100A/μs		15		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-2.0A, di/dt=100A/μs		8		nC
SCHOTTKY PARAMETERS						
V _F	Forward Voltage Drop	I _F =0.5A		0.39	0.5	V
I _{rm}	Maximum reverse leakage current	V _R =16V			0.1	mA
		V _R =16V, T _J =125°C			20	
C _T	Junction Capacitance	V _R =10V		34		pF
t _{rr}	SchottkyReverse Recovery Time	I _F =1A, di/dt=100A/μs		5.2	10	ns
Q _{rr}	Schottky Reverse Recovery Charge	I _F =1A, di/dt=100A/μs		0.8		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in ² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating. Rev3: Nov. 2010

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MOSFET TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

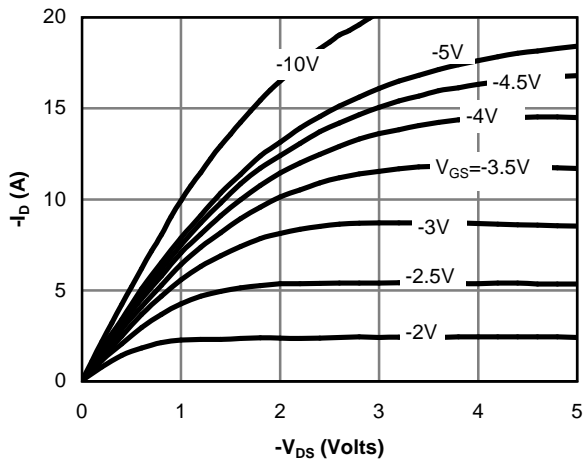


Fig 1: On-Region Characteristics

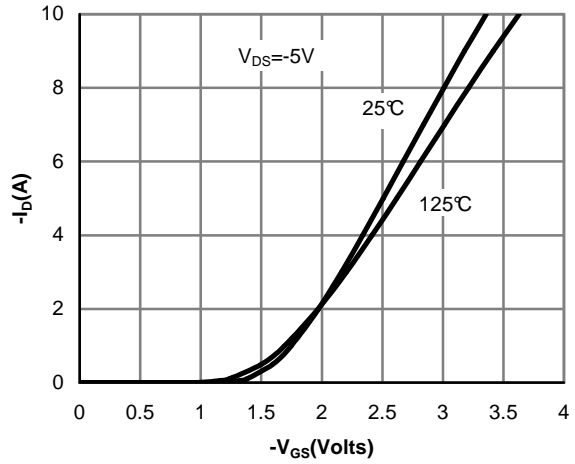


Figure 2: Transfer Characteristics

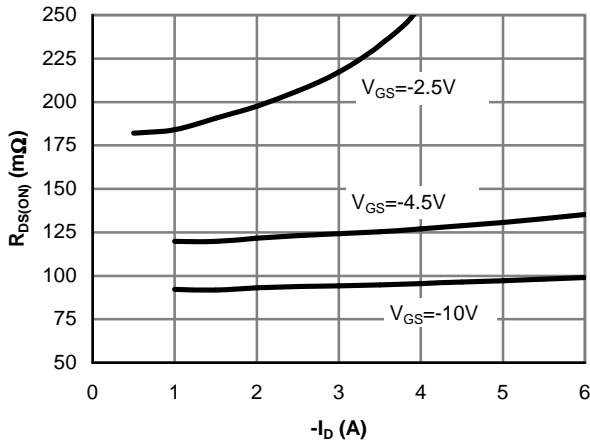


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

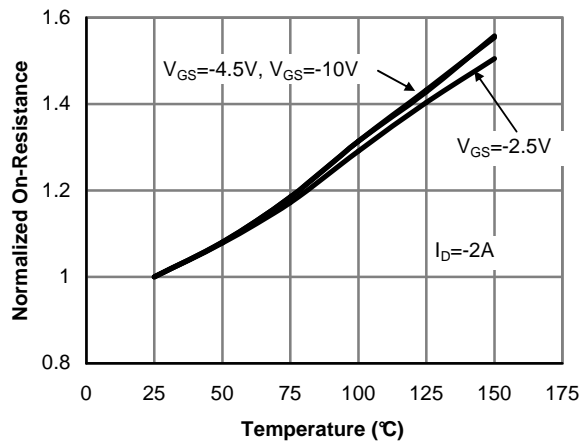


Figure 4: On-Resistance vs. Junction Temperature

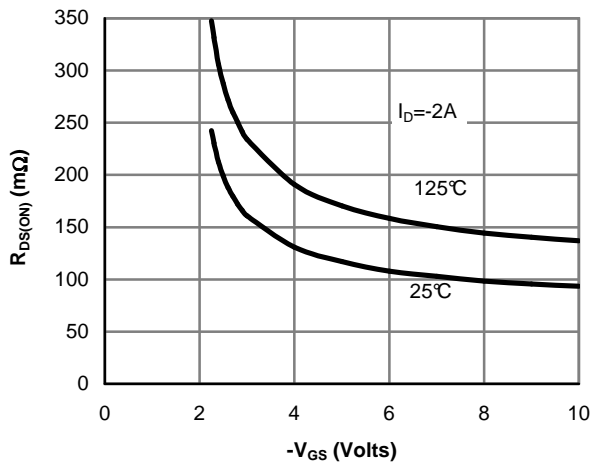


Figure 5: On-Resistance vs. Gate-Source Voltage

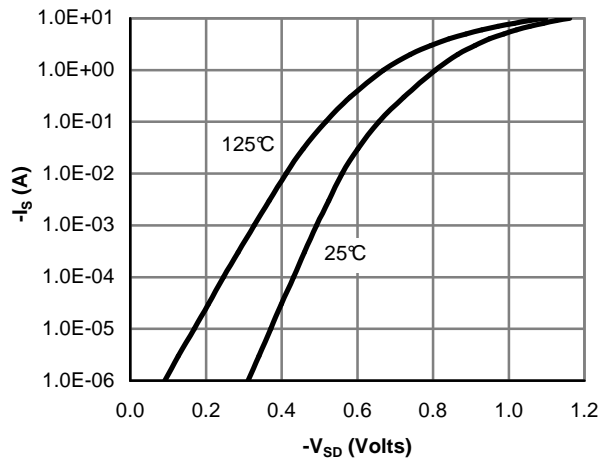


Figure 6: Body-Diode Characteristics

MOSFET TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

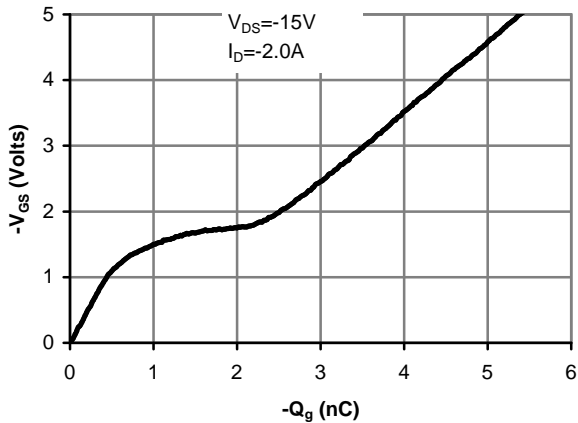


Figure 7: Gate-Charge Characteristics

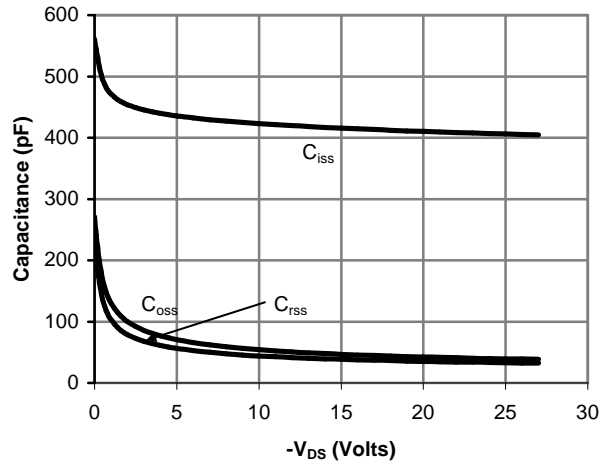


Figure 8: Capacitance Characteristics

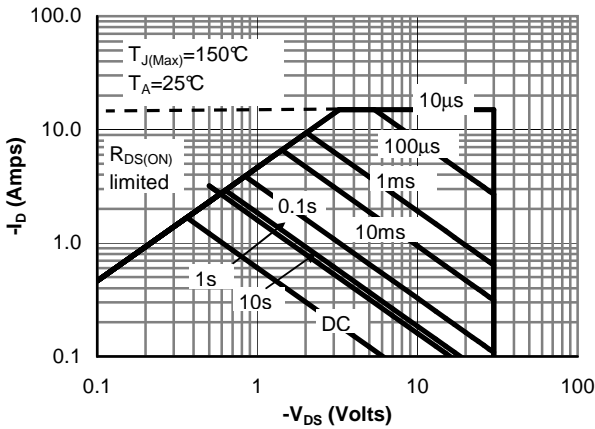


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

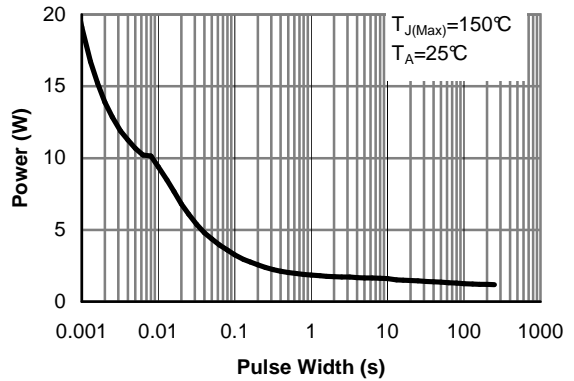


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

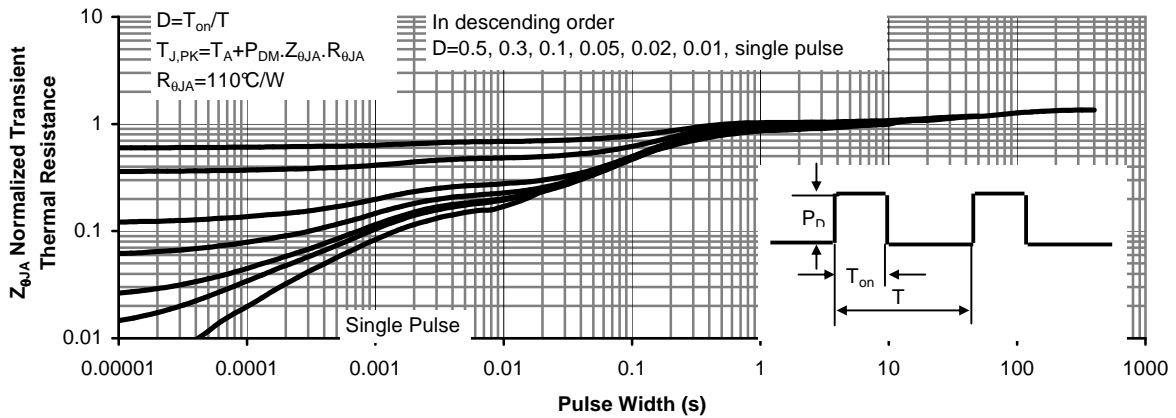


Figure 11: Normalized Maximum Transient Thermal Impedance